

ABSTRACT OF THE DISCLOSURE

A semiconductor structure includes a substrate, a dielectric layer disposed on the substrate, a layer of undoped silicate glass disposed on the dielectric layer, a layer of borophosphorous silicate glass on the layer of undoped silicate glass, and a planar dielectric layer disposed on the layer of borophosphorous silicate glass, the layers of undoped silicate glass, borophosphorous silicate glass, and planar dielectric together forming a pre-metal dielectric stack. The planar dielectric may include plasma-enhanced tetraethyl orthosilicate.

(850063.529D1 / 441716)